

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)	PATENT APPLICATION
)	
Inventors: Sheng Teng Hsu and)	
Fengyan Zhang)	
)	
Serial No.: Not Yet Assigned)	Attorney Docket No.
)	SLA 0819
Filed: Herewith)	
)	
Title: ASYMMETRIC-AREA MEMORY)	
CELL)	
)	

Honorable Commissioner for Patents
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Sir:

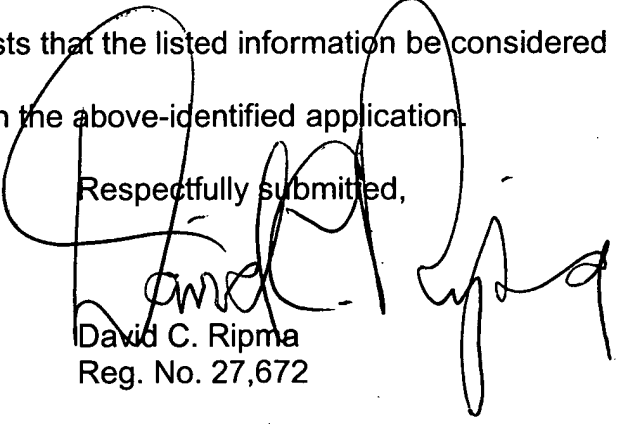
Listed on attached Form PTO-1449 is information submitted pursuant to
37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by
the Examiner and made of record in the above-identified application.

(Date)

12/8/03

Respectfully submitted,


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FORM PTO-1449		DOCKET NUMBER SLA819		APPLICATION NUMBER		
INFORMATION DISCLOSURE CITATION IN AN APPLICATION		APPLICANT Hsu et al.				
		FILING DATE: December 8, 2003		GROUP ART UNIT		
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FIL. DATE IF APPROP.
FOREIGN PATENT DOCUMENTS						
	DOCUMENT NUMBER	DATE	COUNTRY/NAME	CLASS	SUB CLASS	TRANSLATION YES NO
OTHER DOCUMENTS						
	S. Q. Liu, N. J. Wu, and A. Ignatiev, Electrical-pulse-induced reversible resistance change effect in magnetoresistive films” APL. Vol.76, #19, p.2749					
EXAMINER			DATE CONSIDERED			